

# Minghua Wang

## List of Publications by Year in descending order

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Version: 2024-02-01

13  
papers

373  
citations

1163117

8  
h-index

1199594

12  
g-index

13  
all docs

13  
docs citations

13  
times ranked

378  
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoluminescence of Si-rich silicon nitride: Defect-related states and silicon nanoclusters. Applied Physics Letters, 2007, 90, 131903.	3.3	124
2	On Electric Field Induced Breakdown of Passive Films and the Mechanism of Pitting Corrosion. Journal of the Electrochemical Society, 1993, 140, 3448-3457.	2.9	60
3	Electroluminescence of SnO <sub>2</sub> -p-Si heterojunction. Applied Physics Letters, 2008, 92, .	3.3	55
4	Potential Distribution, Shape Evolution, and Modeling of Pit Growth for Ni in Sulfuric Acid. Journal of the Electrochemical Society, 1995, 142, 2986-2995.	2.9	43
5	Correlation between luminescence and structural evolution of Si-rich silicon oxide film annealed at different temperatures. Journal of Applied Physics, 2007, 101, 103504.	2.5	29
6	Photoluminescence of Tb <sup>3+</sup> doped SiN <sub>x</sub> films grown by plasma-enhanced chemical vapor deposition. Journal of Applied Physics, 2006, 100, 083106.	2.5	25
7	Enhanced photoluminescence of Tb <sup>3+</sup> in SnO <sub>2</sub> film by phosphorus diffusion process. Journal of Alloys and Compounds, 2009, 474, 246-249.	5.5	11
8	Localized surface plasmon resonance enhanced photoluminescence from SiN <sub>x</sub> with different N/Si ratios. Optical Materials Express, 2012, 2, 1437.	3.0	8
9	Photoluminescence of Tb <sup>3+</sup> -doped SiN <sub>x</sub> films with different Si concentrations. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 126-130.	3.5	6
10	An Iteration Method for the Computation of Potential and Current Distributions at a Partially Passivated Electrode. Journal of the Electrochemical Society, 1999, 146, 2853-2862.	2.9	5
11	Effects of defect, carrier concentration and annealing process on the photoluminescence of silicon pn diodes. Materials Science in Semiconductor Processing, 2007, 10, 173-178.	4.0	4
12	Electron-beam-induced current evidence for room-temperature photoluminescence of silicon pn diode. Vacuum, 2008, 82, 1337-1340.	3.5	3
13	Intense photoluminescence from Eu-doped silicon-rich silicon oxide films prepared by electron beam evaporation. , 2009, , .		0